Electronic Supplementary Material (ESI) for CrystEngComm.
This journal is © The Royal Society of Chemistry 2017

Electronic Supplementary Information for:

Tailoring the epitaxy of Sb_2Te_3 and GeTe thin films using surface passivation

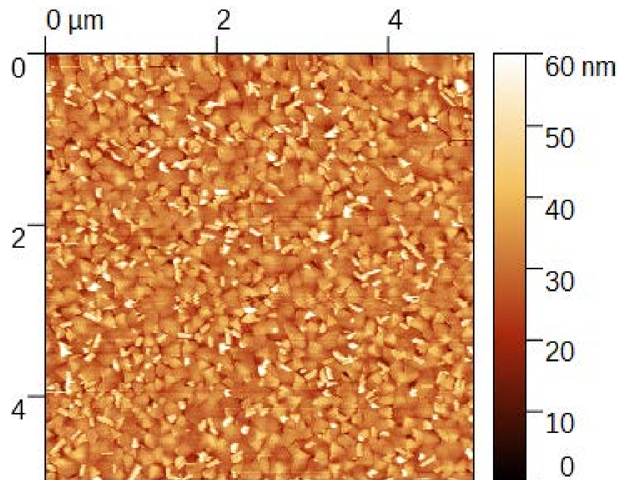
Jamo Momand,[1,] Jos E. Boschker,[2] Ruining Wang,[2] Raffaella Calarco,[2] Bart J. Kooi[1]*

[1]Zernike Institute for Advanced Materials, University of Groningen, Nijenborgh 4, 9747 AG Groningen, The Netherlands

[2]Paul-Drude-Institut für Festkörperelektronik, Hausvogteiplatz 5-7, 10117 Berlin, Germany

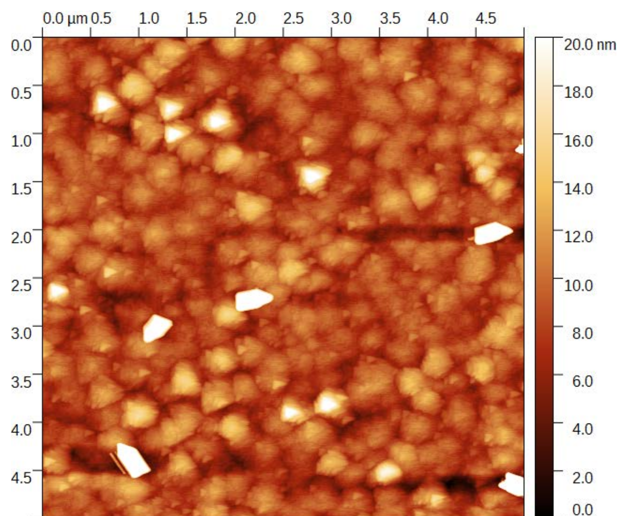
*E-mail: j.momand@rug.nl

AFM scans of Sb_2Te_3 thin films



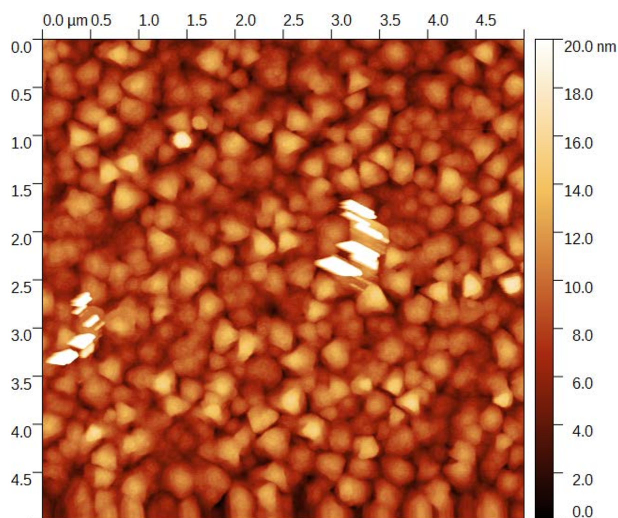
Si(111)-H-Sb_2Te_3

Minimum:	0.000 nm
Maximum:	116.499 nm
Average value:	32.780 nm
Median:	31.918 nm
Ra (Sa):	5.08105 nm
Rms (Sq):	7.15698 nm



Si(111)-Sb_2Te_3

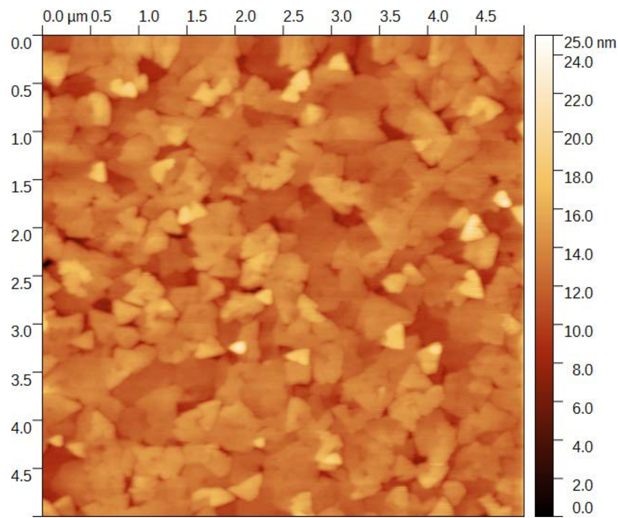
Minimum:	0.0000 nm
Maximum:	44.4545 nm
Average value:	8.9848 nm
Median:	8.6635 nm
Ra (Sa):	1.83423 nm
Rms (Sq):	2.83793 nm



Si(111)-Sb-Sb_2Te_3

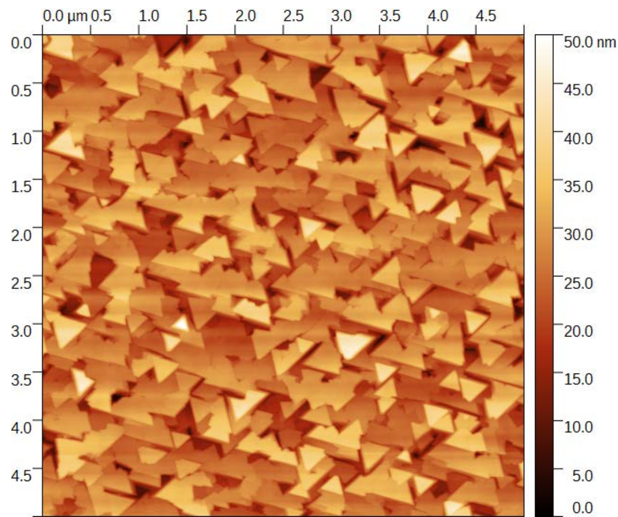
Minimum:	0.0000 nm
Maximum:	46.6280 nm
Average value:	8.0587 nm
Median:	7.6816 nm
Ra (Sa):	2.22414 nm
Rms (Sq):	3.26893 nm

AFM scans of GeTe thin films



Si(111)-H-GeTe

Minimum:	0.0000 nm
Maximum:	22.4203 nm
Average value:	12.8066 nm
Median:	12.8704 nm
Ra (Sa):	1.33648 nm
Rms (Sq):	1.75346 nm



Si(111)-Sb-GeTe

Minimum:	0.0000 nm
Maximum:	50.5738 nm
Average value:	26.3427 nm
Median:	26.5631 nm
Ra (Sa):	4.59487 nm
Rms (Sq):	5.87653 nm